# 600V 75A Insulated Gate Bipolar Transistors

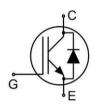
### **FEATURES**

- V<sub>CES</sub>=600V,I<sub>C</sub>=75A(T<sub>C</sub>=100°C)
- · Saturation pressure is reduced and the switching speed is fast
- Saturation pressure drops to a positive temperature coefficient
- High reliability and thermal stability, good parameter consistency

### **APPLICATIONS**

- UPS
- Frequency transformer
- · Industrial power supply
- · Inverter welder

### **SYMBOL**





**TO-247** 

### **ASSEMBLY MESSAGE**

| Product Name | Package | Packaging |
|--------------|---------|-----------|
| BXE75T60HFHD | TO-247  | Tube      |

### **ABSOLUTE MAXIMUM RATINGS** (T<sub>J</sub>=25°C unless otherwise noted)

| Symbol             | Parameter   | Value       | Units |
|--------------------|---|-------------|-------|
| Vces               | Collector-Emitter Voltage                                 | 600         | V     |
| V <sub>GES</sub>   | Gate- Emitter Voltage                                     | ±20         | V     |
| ,                  | Collector Current@Tc = 25 ° C                             | 150         | Α     |
| lc                 | Collector Current @T <sub>C</sub> = 100 ° C               | 75          | Α     |
| I <sub>Cplus</sub> | Pulsed Collector Current, tp limited by Tjmax             | 300         | А     |
|                    | Diode Continuous Forward Current @T <sub>C</sub> = 25 °C  | 150         | Α     |
| l <sub>F</sub>     | Diode Continuous Forward Current @T <sub>C</sub> = 100 °C | 75          | Α     |
| lғм                | Diode Maximum Forward Current                             | 300         | Α     |
| <u> </u>           | Power Dissipation @ T <sub>C</sub> = 25°C                 | 390         | W     |
| $P_D$              | Power Dissipation @ T <sub>C</sub> = 100°C                | 156         | W     |
| $T_J, T_{stg}$     | Operating Junction and Storage Temperature Range          | -55 to +150 | °C    |
| TL                 | Maximum Temperature for Soldering                         | 270         | °C    |

### THERMAL CHARACTERISTICS

| Parameter                                      | Symbol          | Max. | Units |
|--|-----------------|------|-------|
| Thermal Resistance, Junction to case for IGBT  | Rejc            | 0.32 | °C/W  |
| Thermal Resistance, Junction to case for Diode | Rejc            | 0.8  | °C/W  |
| Thermal Resistance, Junction-to-Ambient        | $R_{\theta JA}$ | 45   | °C/W  |



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### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub>=25°C,unless otherwise Noted)

| 0                    | Deuganatan                           | Toot Conditions   | Value |       |      | 1114 - |
|----------------------|--------------------------------------|---|-------|-------|------|--------|
| Symbol               | Parameter                            | Test Conditions   | Min.  | Тур.  | Max. | Units  |
| atic Char            | racteristics                         |   |       |       |      |        |
| V <sub>(BR)CES</sub> | Collector-Emitter Breakdown Voltage  | V <sub>GE</sub> =0V,I <sub>CE</sub> =250uA                            | 600   |       |      | V      |
| I <sub>CES</sub>     | Collector-Emitter Leakage Current    | V <sub>GE</sub> =0V,V <sub>CE</sub> =600V                             |       |       | 1    | mA     |
| I <sub>GES(F)</sub>  | Gate to Emitter Forward Leakage      | V <sub>GE</sub> =+20V,V <sub>CE</sub> =0V                             |       |       | +250 | nA     |
| I <sub>GES(R)</sub>  | Gate to Source Reverse Leakage       | V <sub>GE</sub> =-20V,V <sub>CE</sub> =0V                             |       |       | -250 | nA     |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> =75A,V <sub>GE</sub> =15V                              |       | 1.75  | 2.4  | V      |
| $V_{\text{GE(th)}}$  | Gate Threshold Voltage               | I <sub>C</sub> =250uA,V <sub>CE</sub> =V <sub>GE</sub>                | 4     | 5.5   | 7    | V      |
| ynamic C             | haracteristics                       |   |       |       |      |        |
| Cies                 | Input Capacitance                    | V 20V/V 0V/   |       | 11780 |      |        |
| Coes                 | Output Capacitance                   | V <sub>CE</sub> =30V,V <sub>GE</sub> =0V,                             |       | 253   |      | pF     |
| Cres                 | Reverse Transfer Capacitance         | f=1MHz  |       | 198   |      | -      |
| Qg                   | Total Gate Charge                    |   |       | 430   |      |        |
| Q <sub>ge</sub>      | Gate to Emitter Charge               | V <sub>CE</sub> =480V,I <sub>C</sub> =75A,                            |       | 180   |      | nC     |
| Q <sub>gc</sub>      | Gate to Collector Charge             | V <sub>GE</sub> =15V  |       | 150   |      |        |
| witching             | Characteristics                      |   |       |       |      |        |
| t <sub>d(ON)</sub>   | Turn-on Delay Time                   |   |       | 96    |      |        |
| t <sub>r</sub>       | Rise Time                            |   |       | 92    |      |        |
| t <sub>d(OFF)</sub>  | Turn-Off Delay Time                  | $V_{CE}$ =400V, $I_{C}$ =75A,<br>$V_{GE}$ =15V, $R_{g}$ =7 $\Omega$ , |       | 308   |      | ns     |
| t <sub>f</sub>       | Fall Time                            | Inductive Load,   |       | 59    |      |        |
| Eon                  | Turn-On Switching Loss               | T <sub>J</sub> =25°C  |       | 4.6   |      |        |
| E <sub>off</sub>     | Turn-Off Switching Loss              |   |       | 2.1   |      | mJ     |
| Ets                  | Total Switching Loss                 |   |       | 6.7   |      |        |
| t <sub>d(ON)</sub>   | Turn-on Delay Time                   |   |       | 90    |      |        |
| t <sub>r</sub>       | Rise Time                            |   |       | 95    |      |        |
| $t_{\text{d(OFF)}}$  | Turn-Off Delay Time                  | V <sub>CE</sub> =400V,I <sub>C</sub> =75A,                            |       | 336   |      | ns     |
| <b>t</b> f           | Fall Time                            | $V_{GE}$ =15V, $R_g$ =7 $\Omega$ ,<br>_Inductive Load,                |       | 55    |      |        |
| Eon                  | Turn-On Switching Loss               | T <sub>J</sub> =150°C   |       | 4.3   |      |        |
| E <sub>off</sub>     | Turn-Off Switching Loss              |   |       | 2.3   |      | mJ     |
| Ets                  | Total Switching Loss                 |   |       | 6.6   |      |        |

## ELECTRICAL CHARACTERISTICS OF THE DIODE(TJ=25°C, unless otherwise Noted)

|                  |                                     |                      |      | Rating | ,    |       |
|------------------|-------------------------------------|----------------------|------|--------|------|-------|
| Symbol           | Parameter                           | Test Conditions      |      | Linita |      |       |
|                  |                                     | rest Conditions      | Min. | Тур.   | Max. | Units |
| VF               | Diode Forward Voltage               | I <sub>F</sub> =75A  |      | 1.8    | 2.4  | V     |
| Trr              | Reverse Recovery Time               | I <sub>F</sub> =75A, |      | 65     |      | ns    |
| I <sub>RRM</sub> | Diode Peak Reverse Recovery Current |                      |      | 5      | -    | Α     |
| Q <sub>rr</sub>  | Reverse Recovery Charge             | ui/ul-200A/uS        |      | 195    |      | nC    |

Note: Pulse width ≤ 300µs, Duty cycle ≤ 2%



### TYPICAL PERFORMANCE CHARACTERISTICS

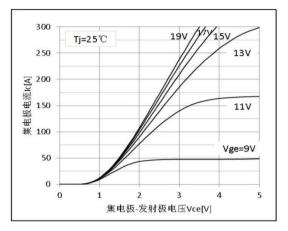


图 1 输出特性曲线

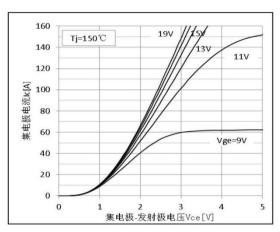


图 2 输出特性曲线

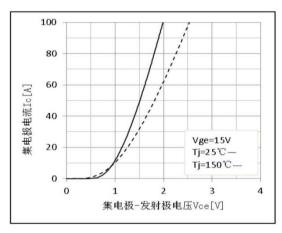


图 3 饱和压降特性

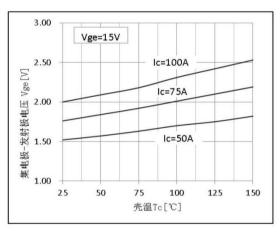


图 4 饱和压降温度特性

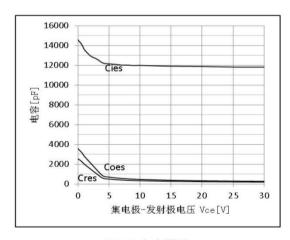


图 5 电容特性

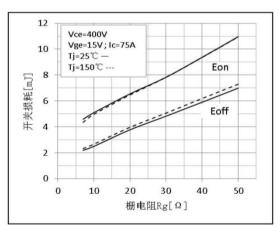


图 6 开关损耗-栅电阻特性曲线

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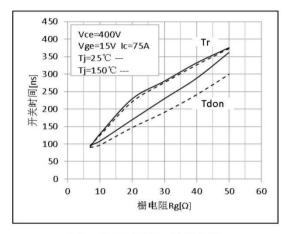


图 7 开通-栅电阻特性曲线

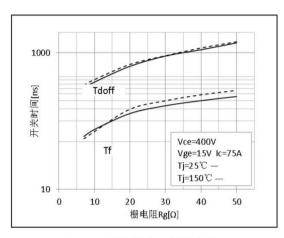


图 8 关断-栅电阻特性曲线

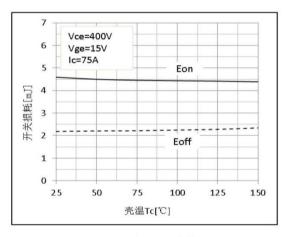


图 9 开关损耗温度特性

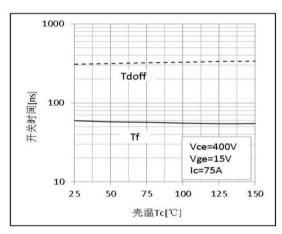


图 10 关断温度特性

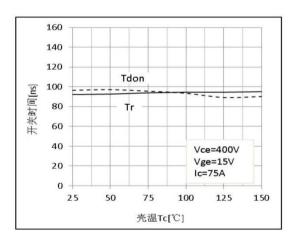


图 11 开通的温度特性

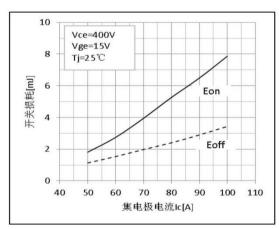


图 12 开关损耗的电流特性



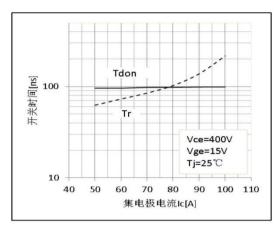


图 13 开通的电流特性

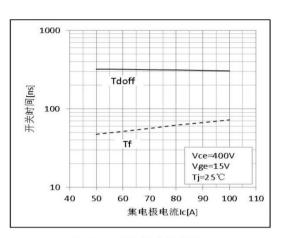


图 14 关断的电流特性

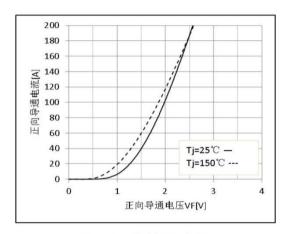


图 15 二极管正向特性

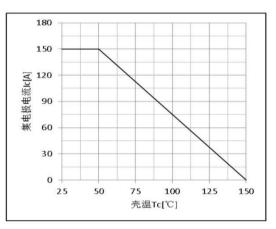


图 16 集电极电流温度特性

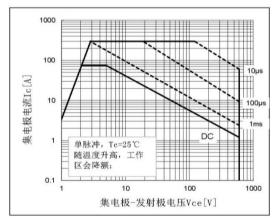


图 17 正向安全工作区

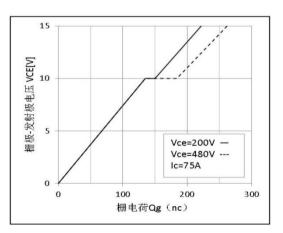
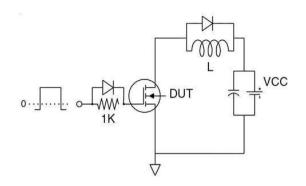


图 18 栅电荷特性



### **TEST CIRCUIT**

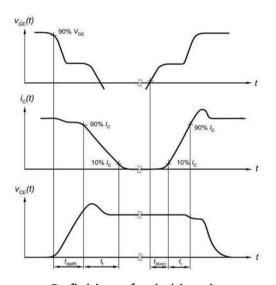


**Gate Charge Test Circuit** 

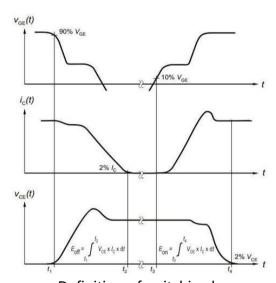
# $V_{DC}$ DUT (Diode) L $C_{\sigma}$ $C_{r}$ $C_{r}$

Switch Time Test Circuit

### **SWITCHING CHARACTERISTICS**

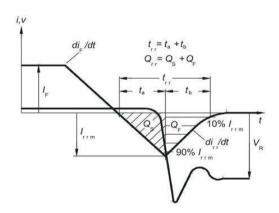


Definition of switching times



Definition of switching losses

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Definition of diode switching characteristics



# **Revision history**

# **Document revision history**

| Date        | Revision | Changes       |
|-------------|----------|---------------|
| 20-Oct-2021 | 1.0      | First release |
|             |          |               |
|             |          |               |
|             |          |               |



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 IGW30N60H3FKSA1
 STGWA8M120DF3
 IGB30N60H3ATMA1
 IGW100N60H3FKSA1
 IGW75N60H3FKSA1
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